

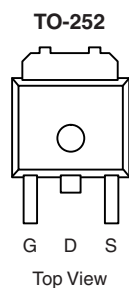
N-Channel 60-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

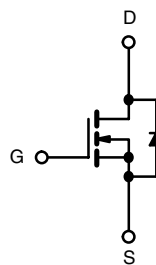
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^c	Q_g (Typ)
60	0.0078 at $V_{GS} = 10$ V	93	94

FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested
- High Threshold at High Temperature


RoHS
COMPLIANT


Ordering Information: SUD50N06-08H0-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C) ^b	I_D	$T_C = 25$ °C	93 ^c
		$T_C = 125$ °C	54 ^c
Pulsed Drain Current	I_{DM}	100	A
Continuous Source Current (Diode Conduction)	I_S	91 ^c	
Avalanche Current, Single Pulse	I_{AS}	50	
Avalanche Energy	E_{AS}	125	mJ
Maximum Power Dissipation	P_D	$T_C = 25$ °C	136 ^b
		$T_A = 25$ °C	3 ^a
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	15	°C/W
		Steady State	40	
Junction-to-Case	R_{thJC}	0.85	1.1	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. See SOA curve for voltage derating.

c. Calculate continuous current based on maximum allowable junction temperature when using infinite heat sink. Package limitation current is 50 A.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	3.4		4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0065	0.0078	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.013	
		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.0156	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A		25		S
Dynamic ^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, F = 1 MHz		7000		pF
Output Capacitance	C _{oss}			450		
Reverse Transfer Capacitance	C _{rss}			240		
Gate Resistance	R _g	f = 1 MHz	0.75	1.5	2.3	Ω
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 50 A		94	145	nC
Gate-Source Charge ^c	Q _{gs}			35		
Gate-Drain Charge ^c	Q _{gd}			20		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.6 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω		28	45	ns
Rise Time ^c	t _r			13	20	
Turn-Off Delay Time ^c	t _{d(off)}			50	75	
Fall Time ^c	t _f			10	15	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)						
Pulsed Current	I _{SM}				100	A
Diode Forward Voltage ^b	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.0	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		45	70	ns

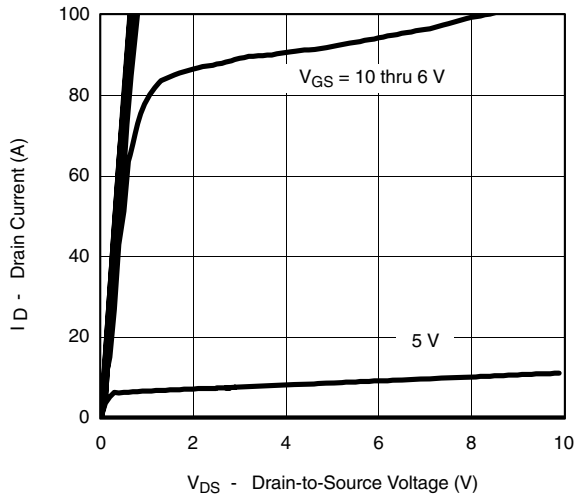
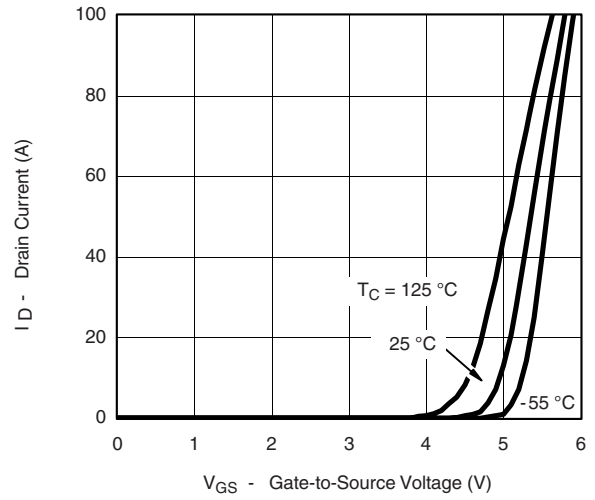
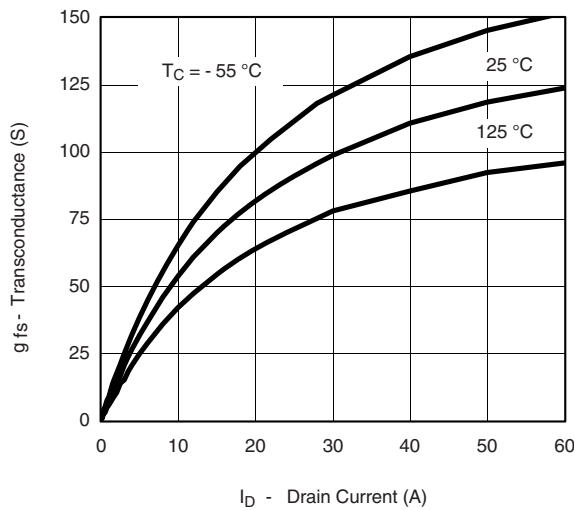
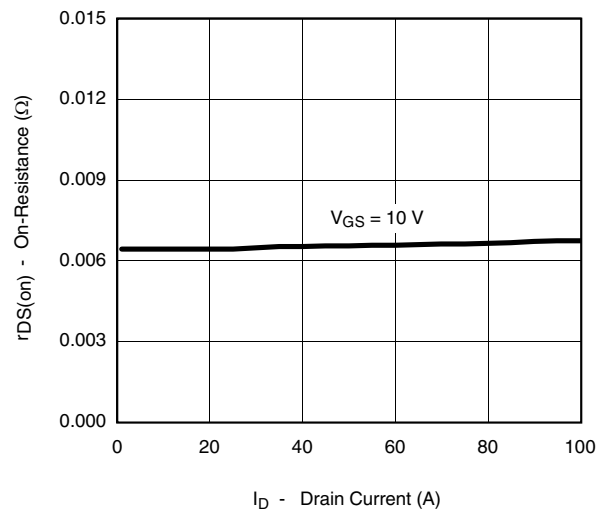
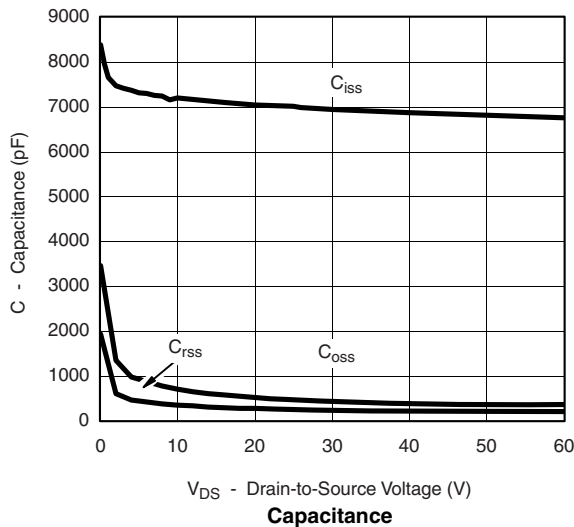
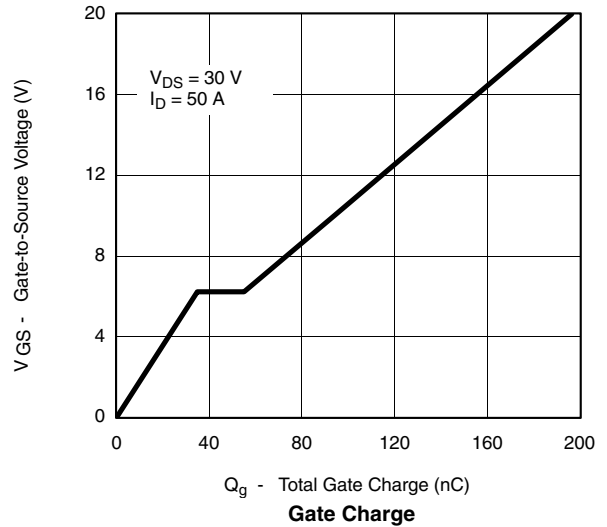
Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

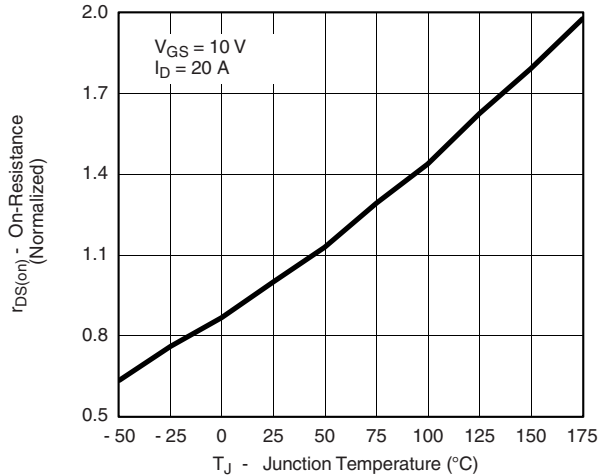
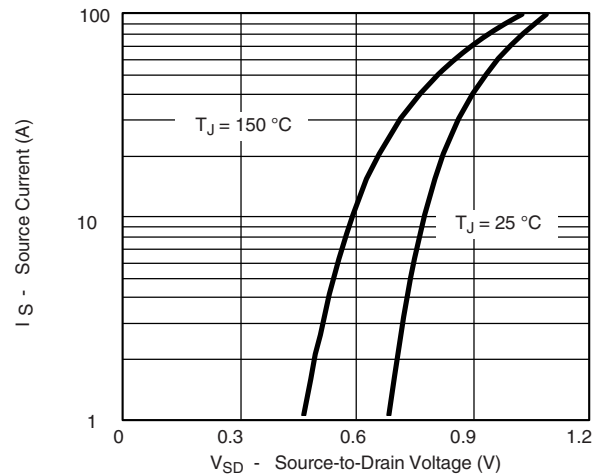
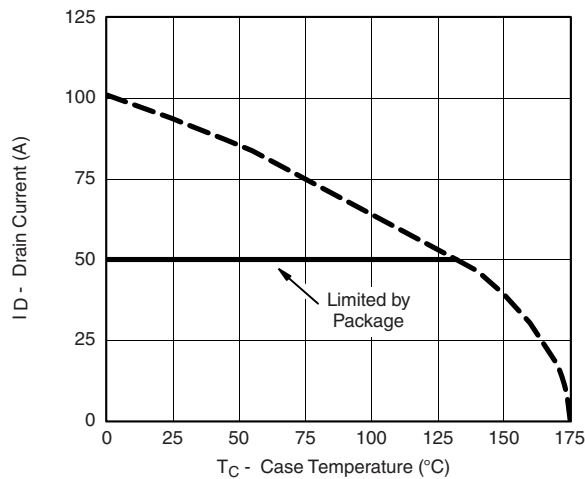
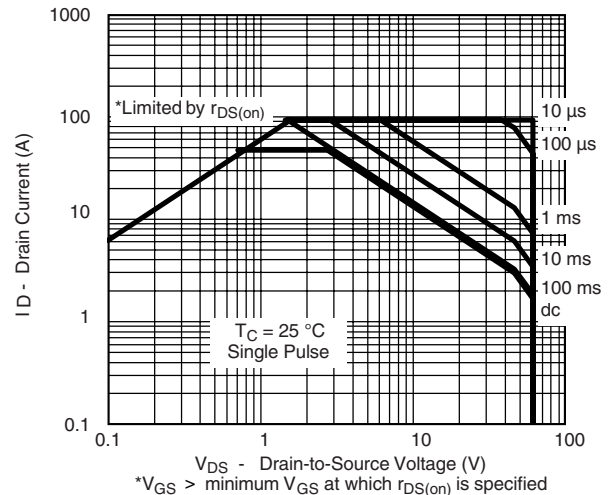
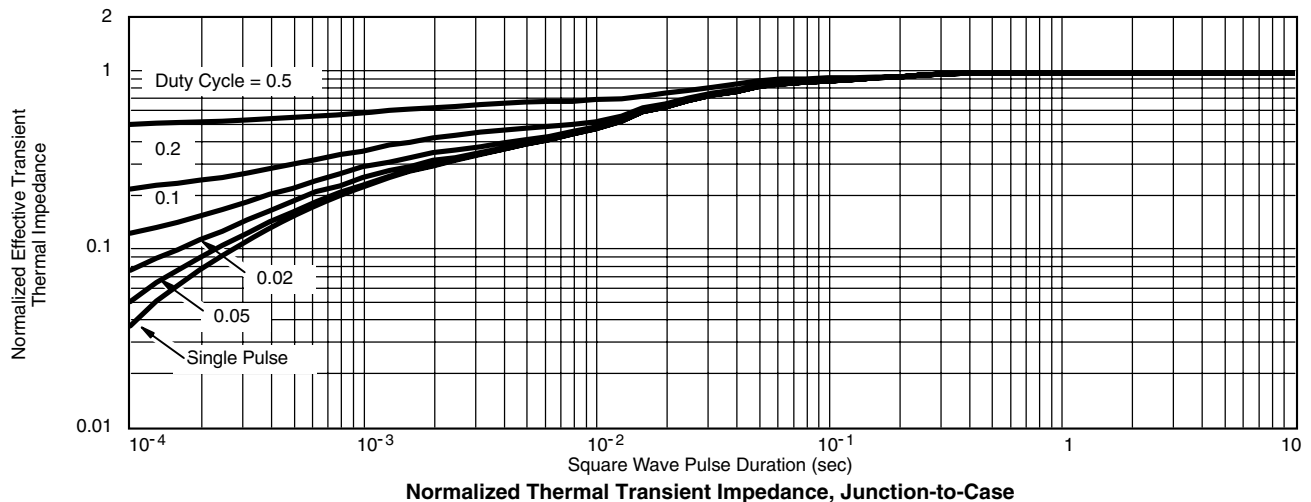
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

SUD50N06-08H

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****THERMAL RATINGS****Maximum Avalanche Drain Current vs. Case Temperature****Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Case**

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